

Am27X2048

ADV MICRO (MEMORY)

2 Megabit (131,072 x 16-Bit) CMOS ExpressROM™ Device

Advanced Micro **Devices**

DISTINCTIVE CHARACTERISTICS

- As an OTP EPROM alternative:
 - Factory optimized programming
 - Fully tested and guaranteed
 - Lower cost
- As a Mask ROM alternative:
 - Shorter leadtime
 - Lower volume per code
- Compatible with JEDEC-approved EPROM pinout

- **High noise immunity**
- **High performance CMOS technology**
 - Fast access time 150 ns
 - Low power dissipation 100 µA maximum standby current
- Available in plastic DIP and plastic leaded chip carrier (PLCC), and in DIE form
- Latch-up protected to 100 mA from -1 V to Vcc + 1 V

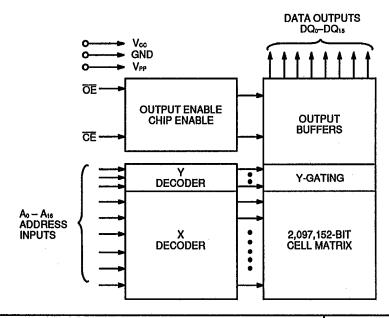
GENERAL DESCRIPTION

The Am27X2048 is a wafer-level programmed EPROM with a standard topside for plastic packaging. It is organized as 131,072 by 16 bits and is available in plastic DIP as well as plastic leaded chip carrier (PLCC) packages. ExpressROM Devices provide a board-ready memory solution for medium to high volume codes with short leadtimes. This offers manufacturers a cost-effective and flexible alternative to OTP EPROMs and mask programmed ROMs.

Access times as fast as 150 ns allow operation with high-performance microprocessors with reduced WAIT states. The Am27X2048 offers separate Output Enable (OE) and Chip Enable (CE) controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMD's CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 125 mW in active mode, and 125 µW in standby mode.

BLOCK DIAGRAM



12081B-001

Publication # 15653 Rev. A Amendment/0

Issue Date: Merch 1991

±5% VCC Tolerance

±10% VCC Tolerance

Family Part No.

Ordering part No:

Max Access Time (ns)

CE (E) Access (ns)

OE (G) Access (ns)

-155

150

150

65

200

75

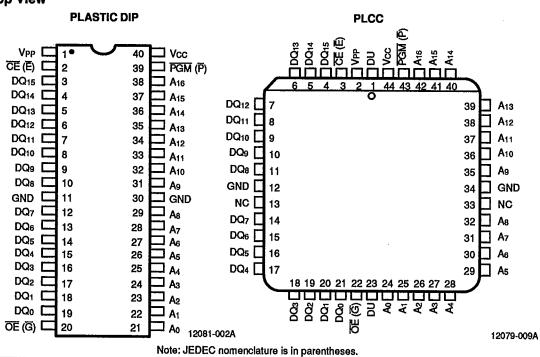
PRODUCT SELECTOR GUIDE

	T-46-13-25
Am27X2048	
-205	
-200	-250
200	250

250

100

CONNECTION DIAGRAMS Top View





Ao - A16 DQ0 - DQ15 CE (E) ŌĒ(G) 12081B-004

PIN DESCRIPTION

An - A16 = Address Inputs CE (E) = Chip Enable Input DQ0 - DQ15 = Data Outputs ŌE (G) = Output Enable Input PGM (P) = Enable input Vpp = Vcc Supply Voltage Vcc Vcc Supply Voltage **GND** Ground NC No Internal Connection DU No External Connection (Do Not Use)

ORDERING INFORMATION Standard Products

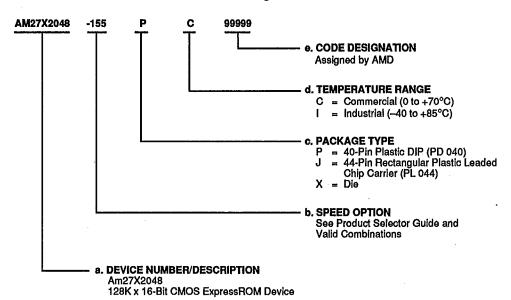
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AMD standard products are available in several packages and operating ranges. The ordering number (Valid Combination) is formed by a combination of:

a. Device Number

b. Speed Option

- c. Package Type d. Temperature Range e. Code Designation



Valid Combinations					
AM27X2048-155 AM27X2048-200 AM27X2048-205 AM27X2048-250	PC, JC, XC, PI, JI				

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

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FUNCTIONAL DESCRIPTION Read Mode

The Am27X2048 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (CE) is the power control and should be used for device selection. Output Enable (OE) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (tacc) is equal to the delay from \overline{CE} to output (tce). Data is available at the outputs to after the falling edge of OE, assuming that CE has been LOW and addresses have been stable for at least tacc - toE.

Standby Mode

The Am27X2048 has a CMOS standby mode which reduces the maximum Vcc current to 200 µA. It is placed in CMOS-standby when \overline{CE} is at $Vcc \pm 0.3$ V. The Am27X2048 also has a TTL-standby mode which reduces the maximum Vcc current to 1.0 mA. It is placed in TTL-standby when \overline{CE} is at V_{IH}. When in standby mode, the outputs are in a high-impedance state, independent of the OE input.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- 1. Low memory power dissipation, and
- Assurance that output bus contention will not occur.

It is recommended that CE be decoded and used as the primary device-selecting function, while OE be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular

System Applications

memory device.

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1 µF ceramic capacitor (high frequency, low inherent inductance) should be used on each device between Vcc and GND to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on ExpressROM Device arrays, a 4.7 µF bulk electrolytic capacitor should be used between Vcc and GND for each eight devices. The location of the capacitor should be close to where the power supply is connected to the

Mode Select Table							
Pins Mode	CE	ŌĒ	PGM	V pp	Outputs		
Read	VIL	VIL	х	х	Dour		
Output Disable	ViL	VIH	х	х	High Z		
Standby (TTL)	VIH	х	x	×	High Z		
Standby (CMOS)	Vcc ± 0.3 V	Х	X	Х	High Z		

Note: X can be either VII or VIII

ABSOLUTE MAXIMUM RATINGS

Storage Temperature

-65 to +125°C

Ambient Temperature

with Power Applied

-55 to +125°C

Voltage with Respect to Ground:

All pins except Vcc

-0.6 to Vcc + 0.6 V

-0.6 to +7.0 V

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

During transitions, the input may overshoot GND to -2.0 V for periods of up to 20 ns. Maximum DC voltage on input and output may overshoot to Vcc +2.0 V for periods of up to 20 ns.

OPERATING RANGES

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Commercial (C) Devices

Case Temperature (Tc)

0 to +70°C

Industrial (i) Devices

Case Temperature (Tc)

-40 to +85°C

Supply Read Voltages:

Vcc for Am27X2048-XX5 Vcc for Am27X2048-XX0

+4.75 to +5.25 V +4.50 to +5.50 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified (Notes 1, 4, 5 & 8)

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Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Unit
TTL and N	MOS				
Vон	Output HIGH Voltage	Іон = 400 μΑ	2.4		٧
Vol	Output LOW Voltage	loL = 2.1 mA		0.45	٧
VH	Input HIGH Voltage		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage		- 0.5	+0.8	٧
lu	Input Load Current	V _{IN} = 0 V to +V _{CC}		1.0	μА
llo	Output Leakage Current	Vout = 0 V to +Vcc		5	μА
lcc1	Vcc Active Current (Note 5)	CE = Va., f = 5 MHz, lout = 0 mA (Open Outputs)		50	mA
lcc2	Vcc Standby Current	CE = VIH		1.0	mA
Ірр	Vcc Supply Current (Note 6)	CE = OE = VIL, VPP = VCC		100	μА
CMOS					
Vон	Output HIGH Voltage	Іон = − 400 μА	Vcc - 0.8		V
Vol	Output LOW Voltage	loL = 2.1 mA		0.45	٧
ViH	Input HIGH Voltage		0.7 Vcc	Vcc+ 0.5	V
ViL	Input LOW Voltage		- 0.5	+0.8	٧
I LI	Input Load Current	Vin = 0 V to +Vcc		1.0	μА
llo	Output Leakage Current	Vout = 0 V to +Vcc		5	μА
lcc ₁	Vcc Active Current (Note 5)	CE = V _k , f = 5 MHz, lout = 0 mA (Open Outputs)		50	mA
lcc2	Vcc Standby Current	CE = Vcc ± 0.3 V		100	μΑ
Ірр	Vcc Supply Current (Note 6)	CE = OE = VIL, VPP = Vcc		100	μА

CAPACITANCE (Notes 2, 3 & 7)

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Parameter Parameter			PD	PD040		PL044	
Symbol	Description	Test Conditions	Тур.	Max.	Тур.	Max.	Unit
Cin	Input Capacitance	Vin = 0 V	10	12	8	10	рF
Соит	Output Capacitance	Vout = 0 V	12	15	9	12	pF

Notes:

- 1. Vcc must be applied simultaneously or before Vpp, and removed simultaneously or after Vpp.
- 2. Typical values are for nominal supply voltages,
- 3. This parameter is only sampled and not 100% tested.
- 4. Caution: The Am27X2048 must not be removed from, or inserted into, a socket or board when Vcc is applied.
- 5. Icc1 is tested with $\overline{OE} = V_{IH}$ to simulate open outputs.
- Maximum active power usage is the sum of Icc and Ipp.
- 7. TA = 25°C, f = 1 MHz.
- 8. During transitions, the input may overshoot GND to -2.0 V for periods of up to 20 ns. Maximum DC voltage on input and output may overshoot to Vcc + 2.0 V for periods of up to 20 ns.

SWITCHING CHARACTERISTICS over operating ranges unless otherwise specified (Notes 1, 3 & 4)

Paramet	er Symbol	Parameter	Test			-205		
JEDEC	Standard	Description	Conditions		-155	-200	-250	Unit
tavov	tacc	Address to Output Delay	CE = OE = VIL	Min. Max.	150	200	250	ns
				Max.	150	200	250	
telav	tce	Chip Enable to	OE = VIL	Min.				ns
		Output Delay		Max.	150	200	250	
tglav	toe	Output Enable to	CE = VIL	Min.				ns
		Output Delay		Max.	65	75	100	
t EHQZ	tor	Chip Enable HIGH		Min.				
tgнqz	(Note 2)	or Output Enable HIGH, whichever comes first, to Out- put Float		Max.	50	60	60	i ns
taxox	tон	Output Hold		Min.	0	0	0	
		from Addresses, CE, or OE, whichever occurred first		Мах.				ns

Notes:

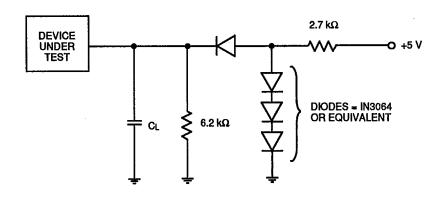
- 1. Vcc must be applied simultaneously or before Vpp, and removed simultaneously or after Vpp.
- 2. This parameter is only sampled and not 100% tested.
- Caution: The Am27X2048 must not be removed from, or inserted into, a socket or board when Vcc is applied.
- 4. Output Load: 1 TTL gate and CL = 100 pF Input Rise and Fall Times: 20 ns

Input Pulse Levels: 0.45 to 2.4 V

Timing Measurement Reference Level-Inputs: 0.8 V and 2 V Outputs: 0.8 V and 2 V

SWITCHING TEST CIRCUIT

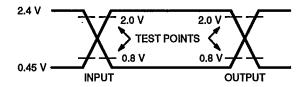
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10205-004A

C_L = 100 pF including jig capacitance

SWITCHING TEST WAVEFORM

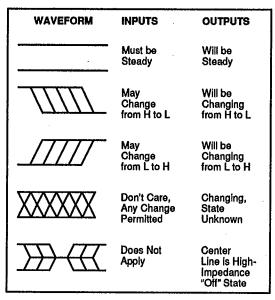


10205-009A

AC Testing: Inputs are driven at 2.4 V for a Logic "1" and 0.45 V for a Logic "0". Input pulse rise and fall times are ≤ 20ns.

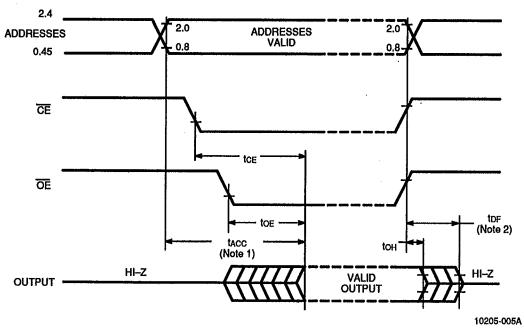
KEY TO SWITCHING WAVEFORMS

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SWITCHING WAVEFORMS



Note:

- 1. OE may be delayed up to tACC-toE after the falling edge of CE without impact on tACC.
- 2. top is specified from $\overline{\text{OE}}$ or $\overline{\text{CE}}$, whichever occurs first.